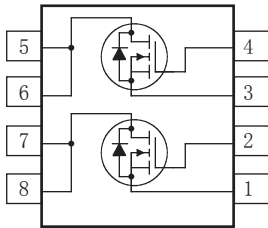
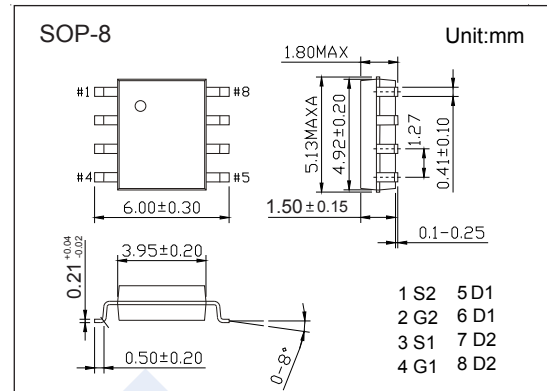


Dual N-Channel MOSFET

FDS6930B (KDS6930B)

■ Features

- $V_{DS} (V) = 30V$
- $I_D = 5.5 A (V_{GS} = 10V)$
- $R_{DS(ON)} < 38m\Omega (V_{GS} = 10V)$
- $R_{DS(ON)} < 50m\Omega (V_{GS} = 4.5V)$
- Fast switching speed
- High power and current handling capability



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	(Note.1) I_D	5.5	A
Pulsed Drain Current	I_{DM}	20	A
Power Dissipation	(Note.1) P_D	2	W
	(Note.2) P_D	1.6	
	(Note.2) P_D	1	
	(Note.3) P_D	0.9	
Thermal Resistance.Junction- to-Ambient	(Note.1) R_{thJA}	78	$^\circ C/W$
Thermal Resistance.Junction- to-Case	R_{thJC}	40	
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature Range	T_{stg}	-55 to 150	

Note.1: $78^\circ C/W$ when mounted on a 0.5 in^2 pad of 2 oz copper

Note.2: $125^\circ C/W$ when mounted on a 0.02 in^2 pad of 2 oz copper

Note.3: $135^\circ C/W$ when mounted on a minimum pad.

Dual N-Channel MOSFET

FDS6930B (KDS6930B)

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V _{DSS}	I _D =250 μA, V _{GS} =0V	30			V
Zero Gate Voltage Drain Current	I _{DSS}	V _D =24V, V _{GS} =0V			1	μA
		V _D =24V, V _{GS} =0V, T _J =55°C			10	
Gate-Body Leakage Current	I _{GSS}	V _D =0V, V _{GS} =±20V			±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _D =V _{GS} , I _D =250μA	1		3	V
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =10V, I _D =5.5A			38	mΩ
		V _{GS} =10V, I _D =5.5A, T _J =125°C			62	
		V _{GS} =4.5V, I _D =4.8A			50	
On State Drain Current	I _{D(ON)}	V _{GS} =10V, V _D =5V	20			A
Forward Transconductance	g _{FS}	V _D =5V, I _D =5.5A		19		S
Input Capacitance	C _{iss}	V _{GS} =0V, V _D =15V, f=1MHz		310	412	pF
Output Capacitance	C _{oss}			90	120	
Reverse Transfer Capacitance	C _{rss}			40	60	
Gate Resistance	R _g	V _{GS} =15V, V _D =0V, f=1MHz		1.9		Ω
Total Gate Charge	Q _g	V _{GS} =5V, V _D =15V, I _D =5.5A		2.7	3.8	nC
Gate Source Charge	Q _{gs}			1		
Gate Drain Charge	Q _{gd}			0.7		
Turn-On DelayTime	t _{d(on)}	V _{GS} =10V, V _D =15V, I _D =1A R _{GEN} =6Ω		6	12	ns
Turn-On Rise Time	t _r			6	12	
Turn-Off DelayTime	t _{d(off)}			16	28	
Turn-Off Fall Time	t _f			2	4	
Body Diode Reverse Recovery Time	t _{rr}	I _F = 5.5A, di/dt= 100A/μs		16	32	nC
Body Diode Reverse Recovery Charge	Q _{rr}			6		
Maximum Body-Diode Continuous Current	I _S				1.3	A
Diode Forward Voltage	V _{SD}	I _S =1A, V _{GS} =0V			1	V

Note. Pulse Test: Pulse Width < 300 μs, Duty Cycle < 2.0%

■ Marking

Marking	6930B KA****
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Dual N-Channel MOSFET FDS6930B (KDS6930B)

Typical Characteristics

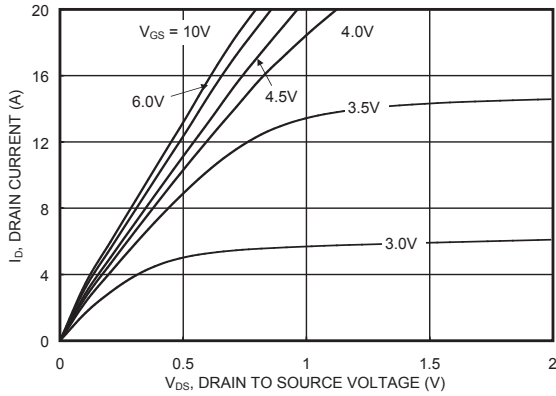


Figure 1. On-Region Characteristics.

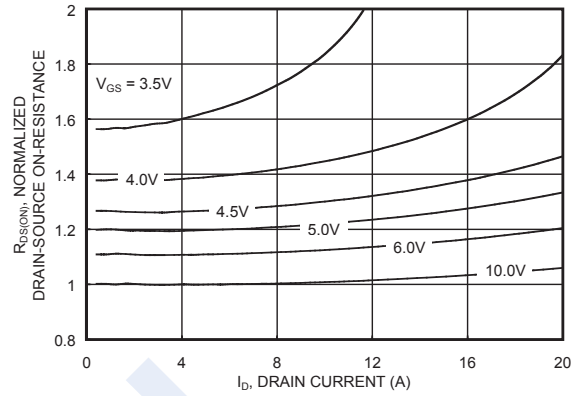


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

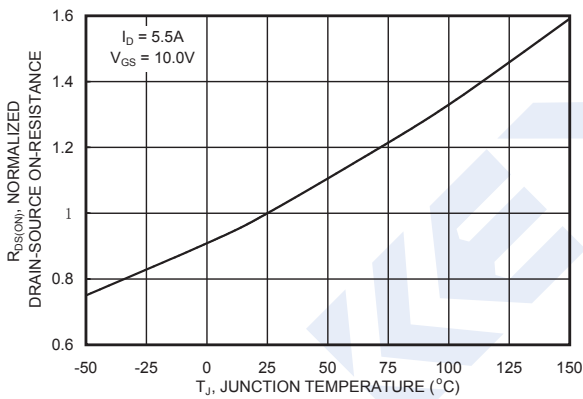


Figure 3. On-Resistance Variation with Temperature.

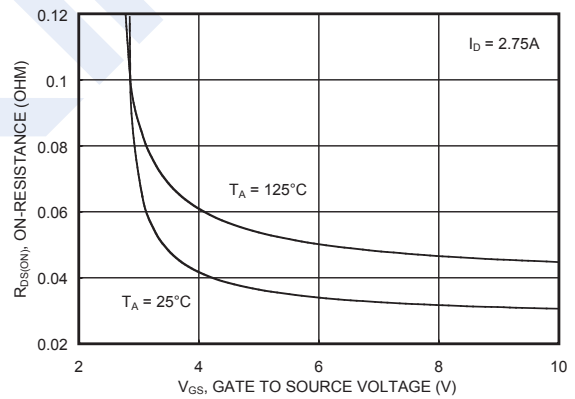


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

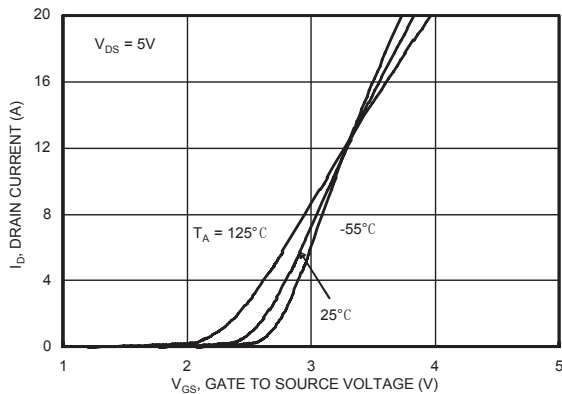


Figure 5. Transfer Characteristics.

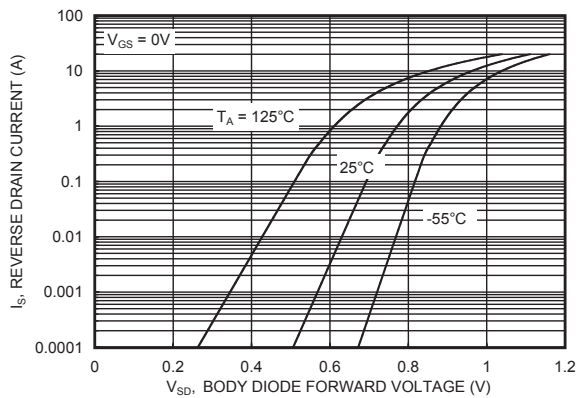


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Dual N-Channel MOSFET FDS6930B (KDS6930B)

Typical Characteristics

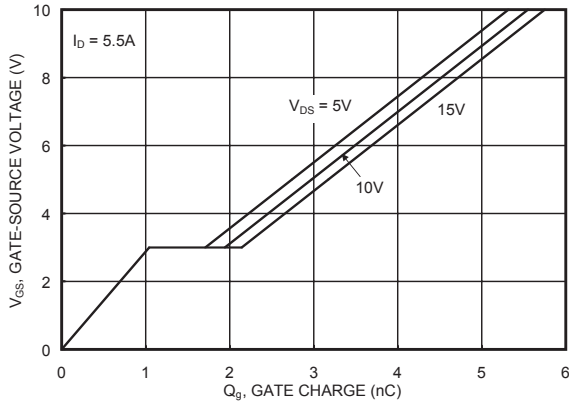


Figure 7. Gate Charge Characteristics.

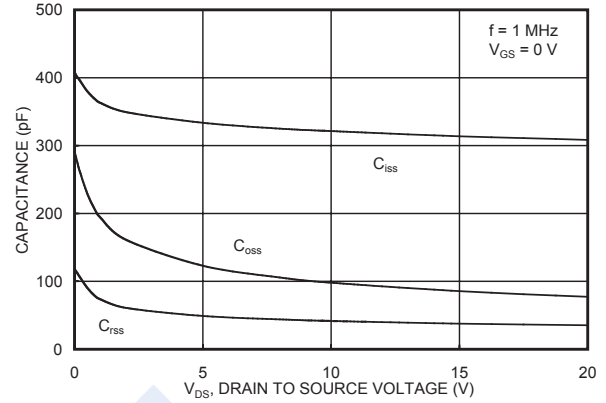


Figure 8. Capacitance Characteristics.

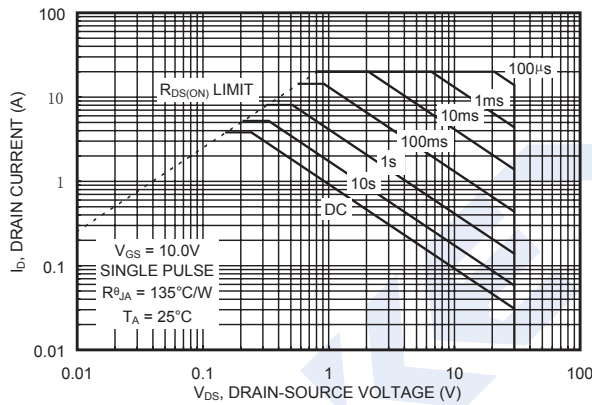


Figure 9. Maximum Safe Operating Area.

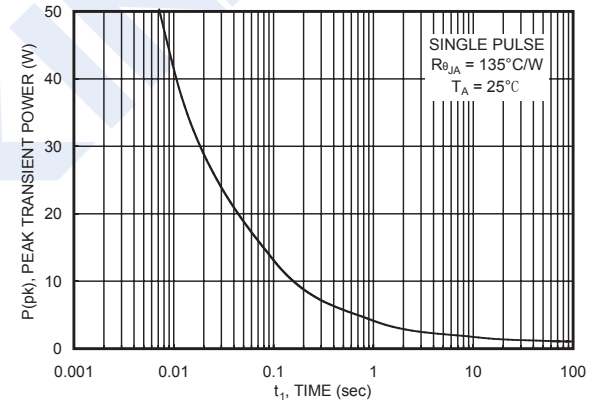


Figure 10. Single Pulse Maximum Power Dissipation.

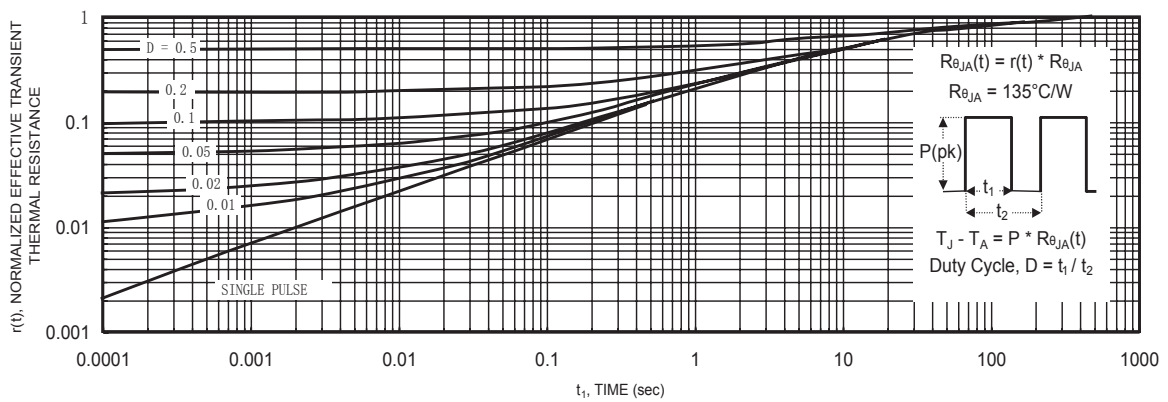


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c. Transient thermal response will change depending on the circuit board design.